

# MAC12SM, MAC12SN



# Description

Designed for industrial and consumer applications for full wave control of AC loads such as appliance controls, heater controls, motor controls, and other power switching applications.

# Features

- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800
  Volts
- On-State Current Rating of 12 Amperes RMS at 80°C

# High Surge Current Capability – 100 Amperes

 Industry Standard TO-220AB Package for Ease of Design

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- Glass Passivated Junctions for Reliability and Uniformity
- These Devices are Pb–Free and are RoHS Compliant

# Pin Out





# **Functional Diagram**



# **Additional Information**









#### **Maximum Ratings** (T<sub>1</sub> = 25°C unless otherwise noted)

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Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, T <sub>J</sub> = -25° to 100°C)	V <sub>drm</sub> , V <sub>rrm</sub>	400 600	V	
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 70^{\circ}$ C)	I <sub>T (RMS)</sub>	12	А	
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_c$ = 125°C)		I <sub>TSM</sub>	90	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	33	A <sup>2</sup> sec	
Peak Gate Power (Pulse Width $\leq$ 1.0 µs, T <sub>c</sub> = 80°C)	P <sub>GM</sub>	16	W	
Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}C$ )		P <sub>G(AV)</sub>	0.35	W
Operating Junction Temperature Range		TJ	-40 to +110	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied.

Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

# **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction–to–Case (AC) Junction–to–Ambient	R <sub>øjc</sub> R <sub>øja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		TL	260	°C

# Electrical Characteristics - OFF (T = 25°C unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Мах	Unit
Peak Repetitive Blocking Current	T, = 25°C	I <sub>DBM</sub> ,	-	-	0.01	
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T_ = 125°C	I	-	-	2.0	mA

#### Electrical Characteristics - ON (T = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic			Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) ( $I_{TM} = \pm 11 \text{ A}$ )		V <sub>TM</sub>	-	1.2	1.85	V
Gate Trigger Current	MT2(+), G(+)		-	13	5.0	
(Continuous dc)	MT2(+), G(-)	I <sub>GT</sub>	-	13	5.0	mA
$(V_{D} = 12 V, R_{L} = 100 \Omega)$	MT2(-), G(-)	1	-	13	5.0	
Holding Current ( $V_p = 12$ V, Gate Open, Initiating Current = ±150 mA))		I <sub>H</sub>	-	30	10	mA
	MT2(+), G(+)	I	-	20	15	mA
Latching Current ( $V_p = 24 V_r I_c = 50 mA$ )	MT2(+), G(-)		-	30	20	
	MT2(-), G(-)		-	20	15	
	MT2(+), G(+)	0.45 0.68	1.5			
Gate Trigger Voltage $(V_{D} = 12 \text{ V}, \text{ R}_{1} = 100 \Omega)$	MT2(+), G(-)	V <sub>gt</sub>	0.45	0.62	1.5	V
	MT2(-), G(-)		0.45	0.67	1.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.



### **Dynamic Characteristics**

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Characteristic	Symbol	Min	Тур	Мах	Unit
Rate of Change of Commutating Current See Figure 10. (V <sub>D</sub> = 400 V, I <sub>TM</sub> = 4.4 A, Commutating dv/dt = 18 V/µs,Gate Open, T <sub>J</sub> = 125°C, f = 250 Hz, No Snubber) C <sub>L</sub> = 10 µF L <sub>L</sub> = 40 mH	dV/dt	8.0	10	_	A/ms
Critical Rate of Rise of Off-State Voltage (VD = Rated VDRM, Exponential Waveform, Gate Open, TJ = 125°C)	dV/dt	15	40	-	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 $\mu$ sec; diG/dt = 100 mA/ $\mu$ sec; lgt = 100 mA; f = 60 Hz	di/dt	-	-	10	A/µs

# Voltage Current Characteristic of SCR

Symbol	Parameter		
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage		
I	Peak Forward Blocking Current		
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage		
I <sub>RRM</sub>	Peak Reverse Blocking Current		
V <sub>TM</sub>	Maximum On State Voltage		
I <sub>H</sub>	Holding Current		



# Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in -phase signals (using standard AC lines) quadrants I and III are used





# Figure 3. Typical Holding Current vs Junction Temperature







Figure 2. Typical Gate Trigger Voltage vs Junction Temperature



Figure 4. Typical Latching Current vs Junction Temperature



#### Figure 6. On-State Power Dissipation









# Figure 8. Typical Thermal Response





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# **Dimensions**



# Part Marking System





Dim	Inches		Millimeters		
Dim	Min	Мах	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
К	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
Ν	0.195	0.205	4.95	5.21	
٥	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
v	0.045		1.15		
Z		0.080		2.04	

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4 No Connection				

Ordering Information					
Device	Package	Shipping			
MAC12SMG	TO-220AB	500 Units / Rail			
MAC12SNG	(Pb-Free)	500 Offits / Hall			

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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